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Comments on “A theoretical study on the linearity of the I_D -T curve of a SiC MESFET for sensor application”

Manas Pal

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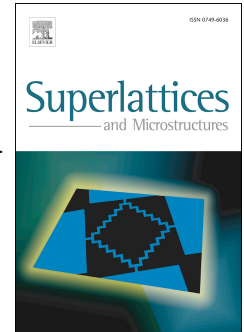
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Manas Pal

Department of Electronics, Netaji Mahavidyalaya,

Arambagh, Hooghly,

West Bengal, India.

ABSTRACT

In this article, the validity of the formulation presented in a recent paper has been questioned. It is pointed out that the built-in potential at the gate of a metal-semiconductor field effect transistor has been erroneously considered, as a result of which the related mathematical formulations and calculations presented in the paper become invalid.

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